

※ 考生請注意：本試題 可 不可 使用計算機

1. (15%)

For the circuit shown in Fig.1, evaluate the following ($\beta=100$):

- (a) The input differential resistance R_{id} .
- (b) The overall differential voltage gain v_o/v_{sig} (neglect the effect of r_o)
- (c) The worst-case common-mode gain if the two collector resistances are accurate to within $\pm 1\%$.
- (d) The CMRR, in dB
- (e) The input common-mode resistance (assuming that the Early voltage $V_A=100V$).

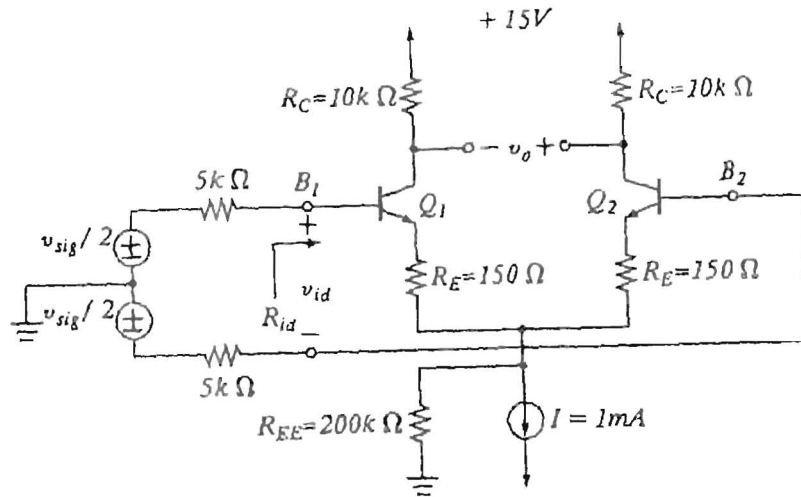


Fig.1

2. (15%)

The network in Fig.2 has $i(t) = 10\cos(50000t)$ mA. Find the steady-state voltages $v(t)$, $v_L(t)$, and $v_C(t)$.

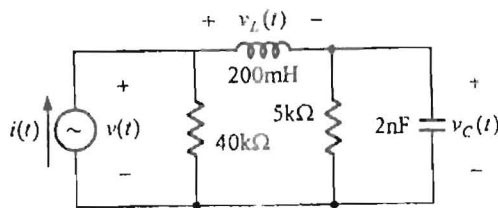


Fig.2

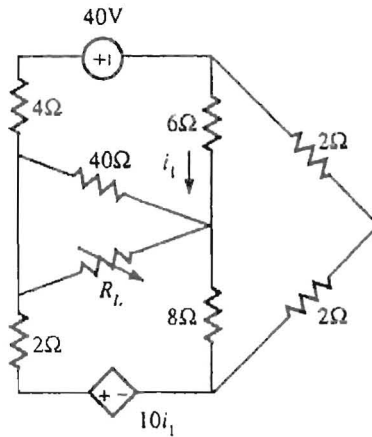


Fig.3

3. (20%)

With the adjustment of the resistor R_L in the circuit of Fig.3, the maximum power delivered to R_L can be achieved. Please calculate the maximum power transferred to R_L ?

4. (20%)

A differential to single-ended amplifier is constructed as shown in Fig.4(a). The amplifier

(背面仍有題目,請繼續作答)

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incorporates Wilson current mirror as active loads. Assuming all of the transistors are in saturation, $\mu_n C_{ox} = 80\mu A/V^2$, $\mu_p C_{ox} = 30\mu A/V^2$, $|V_T| = 0.8V$ for both NMOS and PMOS, $(W/L)_{M1} = (W/L)_{M2} = 320/0.6$, $(W/L)_{M3} = (W/L)_{M4} = (W/L)_{M5} = (W/L)_{M6} = 20/0.9$, $(W/L)_{M7} = 80/0.6$, $(W/L)_{M8} = 160/0.6$. Neglect channel length modulation effect.

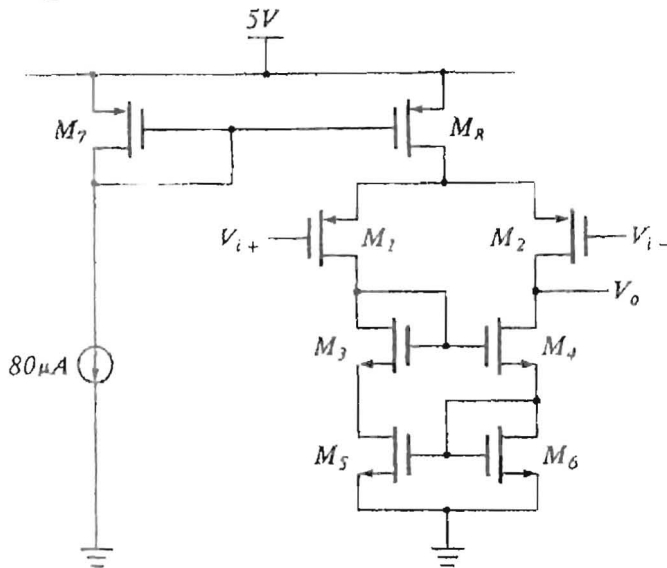


Fig.4(a)

- (a) What kind of feedback mechanism is applied in the Wilson current mirror? (shunt-shunt, series-series, shunt - series, series- shunt)
- (b) Find out the input common mode ranges $V_{icm(max)}$, $V_{icm(min)}$ of this amplifier.
- (c) Consider the circuit shown in Fig.4(b). Assume that $(W/L)_{M3} = (W/L)_{M6} = 21/0.9$, $(W/L)_{M4} = (W/L)_{M5} = 19/0.9$, and the other derives' sizes remain unchanged. If $V_i = 2.5V$, find V_o . (The OP's input offset voltage must be taken into account).
- (d) Follow (c) and neglect all the parasitic capacitances of MOSFETs. If V_i is a rising step from 2V to 3V, find the slew rate of V_o . If V_i is a falling step from 3V to 2V, find the slew rate of V_o .

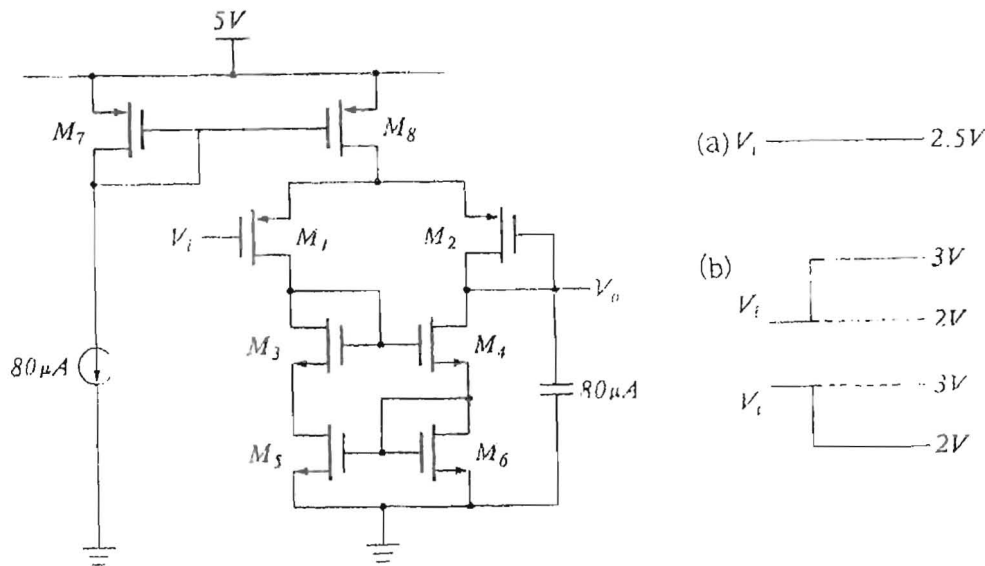


Fig.4(b)

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5. (15%)

Please find the Thévenin and Norton equivalent circuits of the network of Fig.5 at terminals a-b.

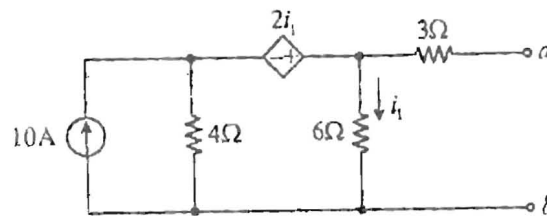


Fig.5

6. (15%)

In the circuit as shown in Fig.6, the junction diode D_1 can be modeled by a forward constant voltage drop of $V_f=0.7V$; the Zener diode D_2 can be modeled by an ideal Zener voltage of $V_Z=3.3V$; the op-amp is ideal; the BJT has parameters $\beta=50$, $V_{BE(on)}=0.7V$, $V_A=\infty$, $V_{CE(sat)}=0.5V$. The resistors are $R_1=R_2=R_3=R_4=R_5=1k\Omega$, $R_6=50\Omega$. The supply voltage is $V_{CC}=12V$

(a) Find the voltage V_1 for $V_{in}=-10V$, $-5V$, $5V$, and $10V$.

(b) Derive the expression for V_{out} as function of V_1 .

(c) Find the value for R_{in} and R_{out} .

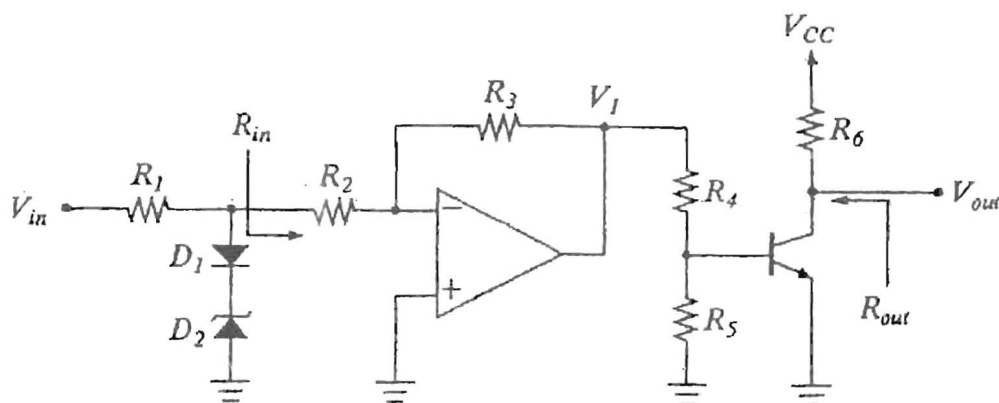


Fig.6